

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L6	4	(gettering adj3 plug)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/16 15:22
2	BRS	L7	219	(gettering adj3 sites)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/16 15:22
3	BRS	L8	118	7 same (impurity or impurities)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/16 15:35
4	BRS	L10	1	getter adj10 impurity adj10 (gettering adj sites)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/16 16:02

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TITLE: SEMICONDUCTOR DEVICE

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[0216] In this state, the resulting substrate is subjected to the step of heat treatment in a nitrogen atmosphere at 400 to 800 degrees centigrade for 1 to 24 hours, for example, at 600 degrees centigrade for 12 hours.

Owing to this step, the introduced impurity elements bestowing the n-conductivity type and the p-conductivity type can be activated. Further, the regions doped with the element phosphorus act as gettering sites, and the catalyst element having remained after the step of the crystallization can be segregated. As a result, the catalyst element can be removed from the channel forming regions. Consequently, the effect of decreasing OFF currents can be brought forth in the TFTs finished up.